

C1
C1 would
these gases; a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas such as He or Ar; a temperature ranging from about 150 to about 600 degrees Celsius, a pressure ranging from about 50 millitorr to about 1 atmosphere (760 torr); and a process time ranging from about 50 to about 500 seconds. Again, one skilled in the art is aware that these parameters can be altered to achieve the same or a similar process.--

In the Claims:

Please cancel claims 17-21 and 76.

Please amend claims 22 and 77-81 as follows:

C2
22. (Twice Amended) A method of forming a capacitor, comprising:
forming a capacitor plate, comprising:
providing a first conductive layer in a first environment;
exposing said first conductive layer to a nitrogen free passivation
gas; and
depositing a second conductive layer over said first conductive
layer, wherein said step of providing a first conductive layer comprises providing a first
conductive layer in an oxygen-free environment; and wherein said step of exposing said first
conductive layer comprises exposing said first conductive layer to a nitrogen free passivation gas
in said oxygen-free environment.

15
27. (Amended) The method of claim 28 wherein the plasma comprises a
selection of N_2/H_2 , N_2 , and NH_3 plasmas.

C3
41
78. (Amended) A method of forming a capacitor, comprising:
forming a capacitor plate, comprising:
providing a first conductive layer in a first environment;
exposing the first conductive layer to a plasma in a second
environment, wherein the first conductive layer is not exposed to oxygen between being

provided in the first environment and being exposed to the plasma in the second environment;
and

depositing a second conductive layer over the first conductive layer.

C3
could
~~79~~

(Amended) A method of forming a capacitor, comprising:

forming a capacitor plate, comprising:

providing a first conductive layer in a first environment;

exposing the first conductive layer to a material selected from the group consisting of B_2H_6 , PH_3 , and a carbon-silicon compound, in a second environment; and

depositing a second conductive layer over the first conductive layer.

~~80~~

(Amended) The method of claim ~~79~~ wherein exposing the first conductive layer comprises exposing the first conductive layer to a carbon-silicon compound selected from the group consisting of CH_3SiH_3 , $(CH_3)_3Si-Si(CH_3)_3$, and HMDS *in situ*.

~~81~~

(Amended) The method of claim ~~79~~ wherein exposing the first conductive layer comprises exposing the first conductive layer to a carbon-silicon compound selected from the group consisting of CH_3SiH_3 , $(CH_3)_3Si-Si(CH_3)_3$, and HMDS *ex situ*.